

N-CHANNEL ENHANCEMENT MODE MOSFET
Product Summary

$V_{(BR)DSS}$	$R_{DS(ON) \text{ max}}$	I_D $T_A = +25^\circ\text{C}$
30V	60mΩ @ $V_{GS} = 10\text{V}$	4 A
	70mΩ @ $V_{GS} = 4.5\text{V}$	3 A

Description

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

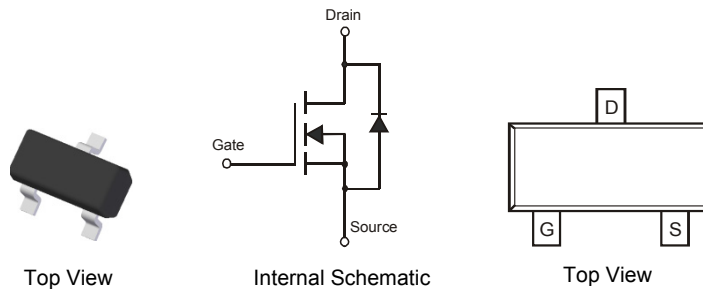
- Backlighting
- Power Management Functions
- DC-DC Converters
- Motor Control

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 standards for High Reliability**

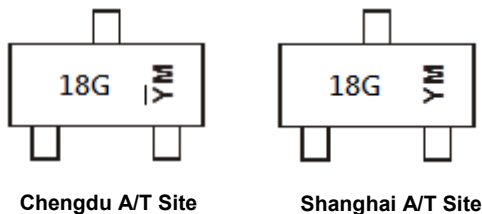
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (approximate)


Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
DMG3418L-7	Standard	SOT23	3000/Tape & Reel
DMG3418L-13	Standard	SOT23	10000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information


18G = Product Type Marking Code
 YM = Date Code Marking for SAT (Shanghai Assembly/ Test site)
 Y̅M = Date Code Marking for CAT (Chengdu Assembly/ Test site)
 Y or Y̅ = Year (ex: A = 2013)
 M = Month (ex: 9 = September)

Date Code Key

Year	2012	2013	2014	2015	2016	2017	2018
Code	Z	A	B	C	D	E	F

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V _{DSS}	30	V
Gate-Source Voltage	V _{GSS}	±12	V
Drain Current (Note 5)	I _D	T _A = +25°C 4.0	A
		T _A = +70°C 3.1	
Drain Current (Note 6)	I _{DM}	Pulsed 15	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	T _A = +25°C 1.4	W
		T _A = +70°C 0.9	
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)	R _{θJA}	90	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 30V, V _{GS} = 0V
Gate-Body Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±12V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	0.5	—	1.5	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(on)}	—	25	60	mΩ	V _{GS} = 10V, I _D = 4A
		—	30	70		V _{GS} = 4.5V, I _D = 3A
		—	50	150		V _{GS} = 2.5V, I _D = 2A
Source-Drain Diode Forward Voltage	V _{SD}	—	—	1.2	V	V _{GS} = 0V, I _S = 2.0A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	464.3	—	pF	V _{DS} = 15V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	49.5	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	43.8	—	pF	
Total Gate Charge	Q _g	—	5.5	—	nC	V _{GS} = 4.5V, V _{DS} = 15V, I _D = 4A
Gate-Source Charge	Q _{gs}	—	1.1	—		
Gate-Drain Charge	Q _{gd}	—	1.8	—		
Turn-On Delay Time	t _{D(on)}	—	1.9	—	ns	V _{DD} = 15V, V _{GEN} = 10V, R _{GEN} = 3Ω, R _L = 3.75Ω
Turn-On Rise Time	t _r	—	1.6	—	ns	
Turn-Off Delay Time	t _{D(off)}	—	10.3	—	ns	
Turn-Off Fall Time	t _f	—	2.0	—	ns	

- Notes:
5. Device mounted on FR-4 PCB with 2oz. Copper and test pulse width t ≤ 10s.
 6. Repetitive rating, pulse width limited by junction temperature.
 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to product testing.

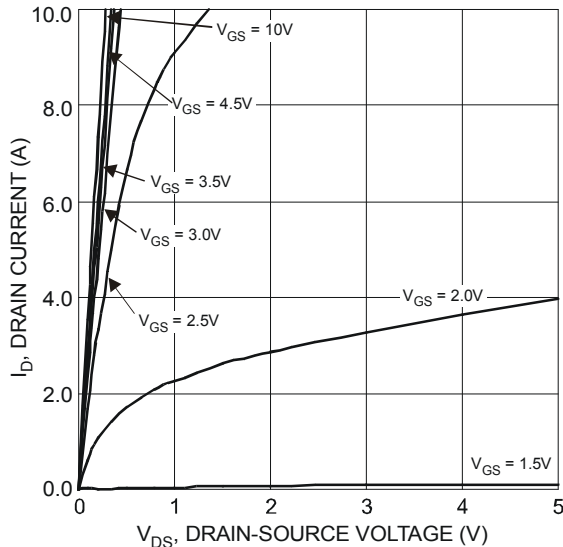


Figure 1 Typical Output Characteristics

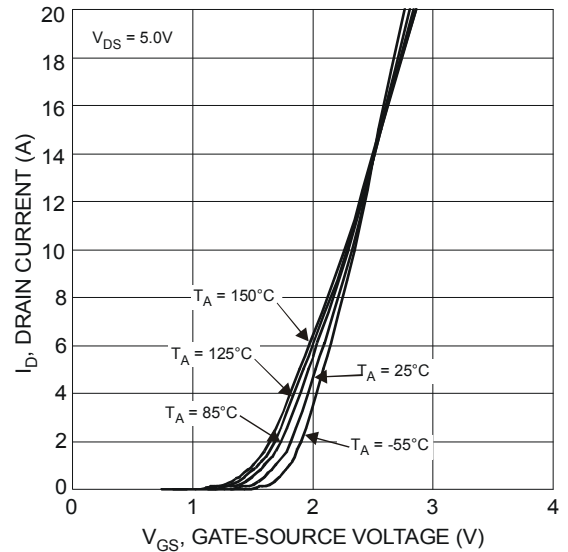


Figure 2 Typical Transfer Characteristics

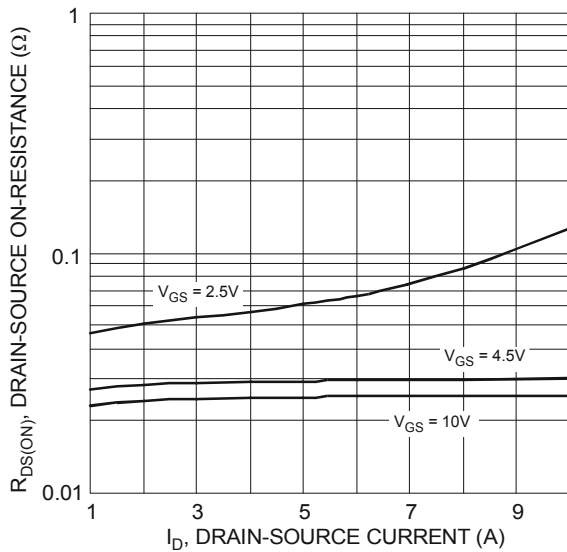


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

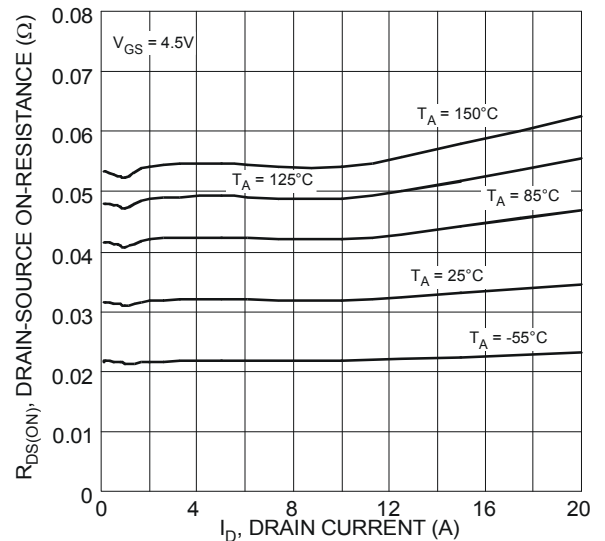


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

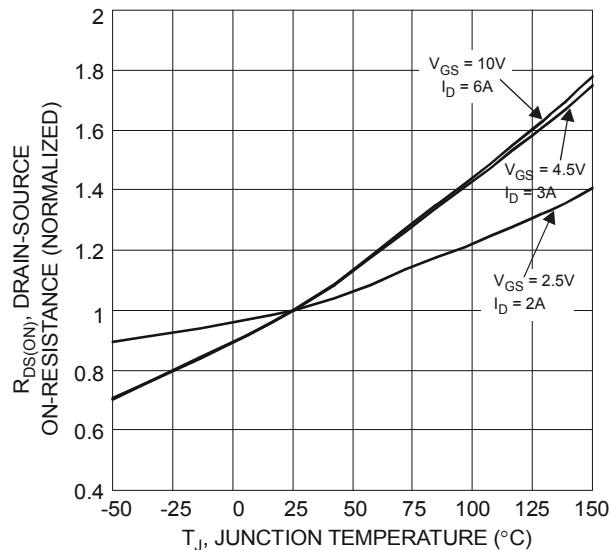


Figure 5 On-Resistance Variation with Temperature

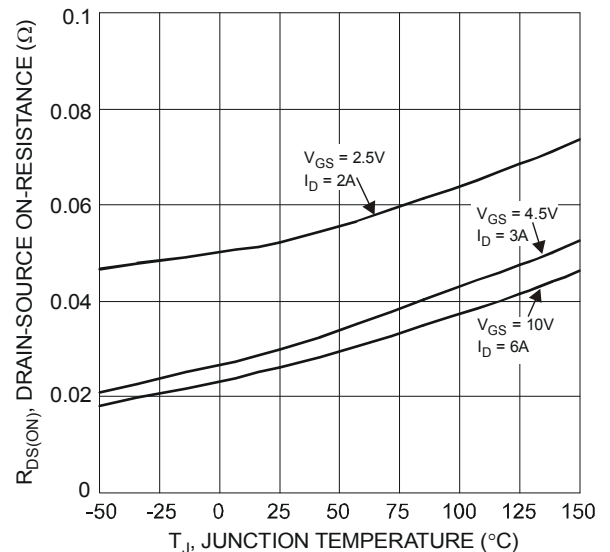


Figure 6 On-Resistance Variation with Temperature

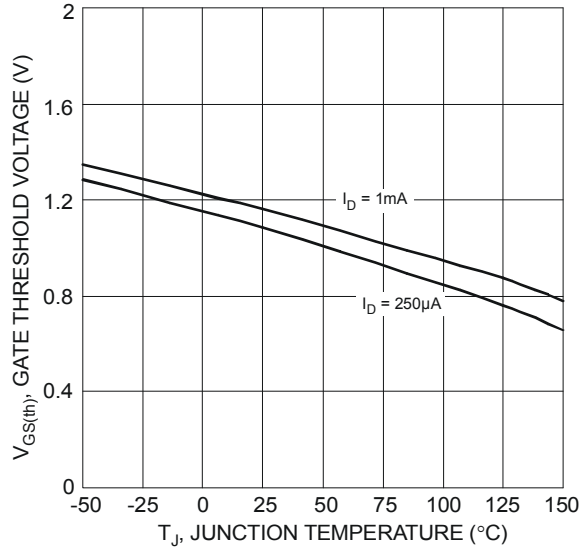


Figure 7 Gate Threshold Variation vs. Ambient Temperature

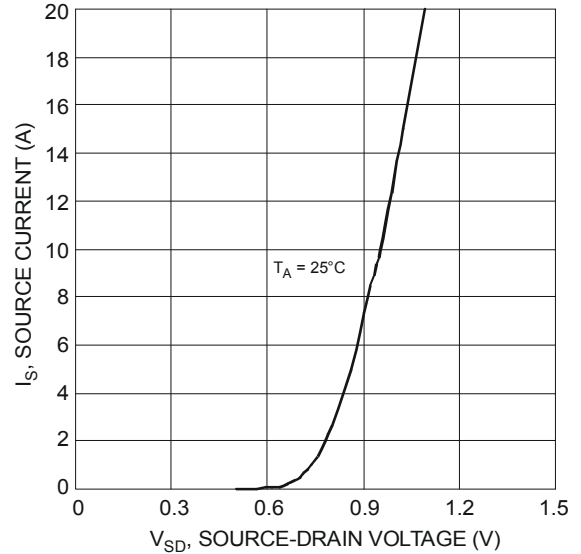


Figure 8 Diode Forward Voltage vs. Current

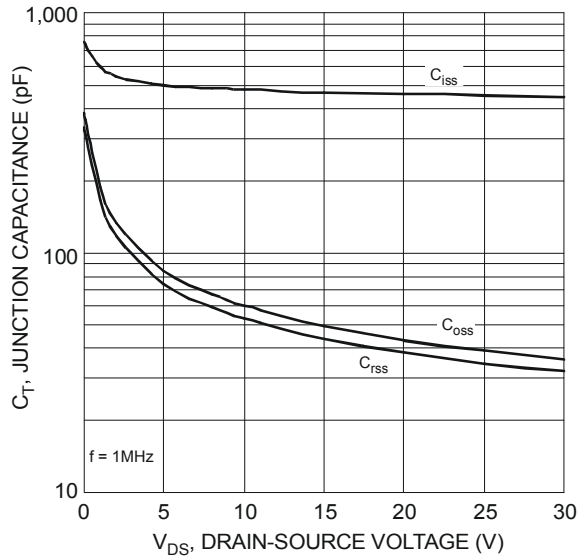


Figure 9 Typical Junction Capacitance

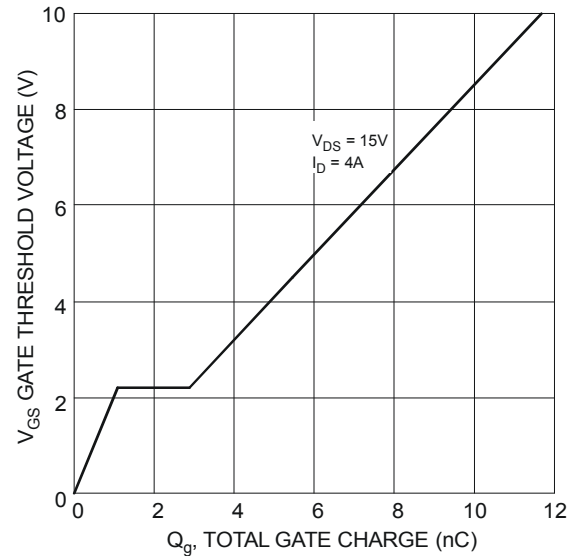
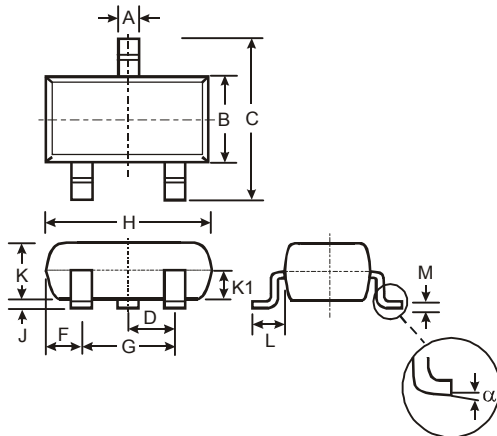


Figure 10 Gate Charge

Package Outline Dimensions

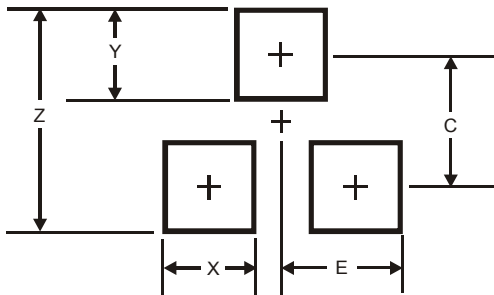
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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